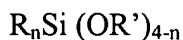


Amendments to the Claims:

1. (Currently amended) A composition for forming a porous film comprising a surfactant, an aprotic polar solvent and a solution comprising a polymer formed by hydrolysis and condensation of one or more silane compounds represented by formula (1):



wherein each R independently represents a linear or branched alkyl group having 1 to 8 carbons or an aryl group, and when there are two or more Rs, ~~the~~ each Rs may be ~~independently~~ the same or different; each R' independently represents an alkyl group having 1 to 4 carbons, and when there are two or more R's, ~~the R's~~ each R' may be ~~independently~~ the same or different; and n is an integer from 0 to 3.

2. (Currently amended) The composition for forming a porous film according to Claim 1 wherein said surfactant is a quaternary ammonium salt which can form a micelle as when dissolved.

3. (Currently amended) The composition for forming a porous film according to Claim 1 ~~or 2~~ wherein said quaternary ammonium salt is an alkyltrimethylammonium salt represented by formula (2):



wherein R'' represents a linear or branched alkyl group having 8 to 20 carbons and X represents an atom or functional group which can form an anion.

4. (Currently amended) The composition for forming a porous film according to Claim 1 ~~or 2~~ wherein said aprotic polar solvent has a dielectric constant of 20 or more.

5. (Currently amended) The composition for forming a porous film according to Claim 1 ~~or 2~~ wherein said aprotic polar solvent is one or more selected from the group consisting of acetonitrile, propionitrile, isobutyronitrile, N-methylpyrrolidone, N, N-dimethylformamide, N,N-dimethylacetamide, dimethylsulfoxide, hexamethylphosphortriamide, nitrobenzene and nitromethane.

6. (Currently amended) A method for manufacturing a porous film comprising the steps of applying ~~said~~ a composition according to Claim 1 ~~or~~ 2 to a substrate so as to form a film thereon, drying the film and transforming the dried film to a porous film by removing said surfactant.

7. (Currently amended) A porous film formable by ~~said~~ a composition according to Claim 1 ~~or~~ 2.

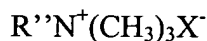
8. (Currently amended) An interlevel insulating film formable by ~~said~~ a composition according to Claim 1 ~~or~~ 2.

9. (Currently amended) A semiconductor device comprising a porous film therein, the porous film being formable by a composition comprising a surfactant, an aprotic polar solvent and a solution comprising a polymer formed by hydrolysis and condensation of one or more silane compounds represented by formula (1): $R_nSi(OR')_{4-n}$

wherein each R independently represents a linear or branched alkyl group having 1 to 8 carbons or an aryl group, and when there are two or more Rs, each ~~the~~ Rs may be independently the same or different; each R' independently represents an alkyl group having 1 to 4 carbons, and when there are two or more R's, ~~the~~ each R's may be independently the same or different; and n is an integer from 0 to 3.

10. (Currently amended) The semiconductor device according to Claim 9 wherein said surfactant is a quaternary ammonium salt which can form a micelle is when dissolved.

11. (Currently amended) The semiconductor device according to Claim 9 ~~or~~ 10 wherein said quaternary ammonium salt is an alkyltrimethylammonium salt represented by formula (2):



wherein R'' represents a linear or branched alkyl group having 8 to 20 carbons and X represents an atom or functional group which can form an anion.

12. (Currently amended) The semiconductor device according to Claim 9 ~~or 10~~ wherein said aprotic polar solvent has a dielectric constant of 20 or more.

13. (Currently amended) The semiconductor device according to Claim 9 ~~or 10~~ wherein said ~~aprotic~~ aprotic polar solvent is one or more selected from the group consisting of acetonitrile, propionitrile, isobutyronitrile, N-methylpyrrolidone, N, N-dimethylformamide, N,N-dimethylacetamide, dimethylsulfoxide, hexamethylphosphortriamide, nitrobenzene and nitromethane.

14. (Currently amended) A semiconductor device according to Claim 9 ~~or 10~~ wherein said porous film is between metal interconnections in a same layer of multi-level interconnects or between upper and lower metal interconnection layers.